



# STGD3NB60KD

N-CHANNEL 6A - 600V - DPAK

SHORT CIRCUIT PROOF PowerMESH™ IGBT

TYPE	V <sub>CES</sub>	V <sub>CE(sat)</sub> (Max) @25°C	I <sub>C</sub> (#) @100°C
STGD3NB60KD	600 V	< 2.8 V	6 A

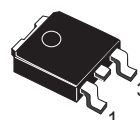
- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW GATE CHARGE
- OFF LOSSES INCLUDE TAIL CURRENT
- HIGH FREQUENCY OPERATION
- SHORT CIRCUIT RATED
- LATCH CURRENT FREE OPERATION
- CO-PACKAGED WITH TURBOSWITCH™ ANTIPARALLEL DIODE

## DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "K" identifies a family optimized for high frequency motor control applications with short circuit withstand capability.

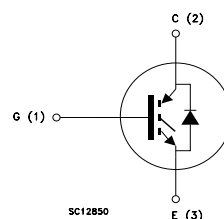
## APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS and PFC



DPAK

## INTERNAL SCHEMATIC DIAGRAM



## ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGD3NB60KDT4	GD3NB60KD	DPAK	TAPE & REEL

## STGD3NB60KD

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-Emitter Voltage (V <sub>GS</sub> = 0)	600	V
V <sub>ECR</sub>	Emitter-Collector Voltage	20	V
V <sub>GE</sub>	Gate-Emitter Voltage	±20	V
I <sub>C</sub>	Collector Current (continuous) at T <sub>C</sub> = 25°C(#)	10	A
I <sub>C</sub>	Collector Current (continuous) at T <sub>C</sub> = 100°C(#)	6	A
I <sub>CM</sub> (■)	Collector Current (pulsed)	24	A
T <sub>sc</sub>	Short Circuit Withstand	10	µs
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	50	W
	Derating Factor	0.4	W/°C
T <sub>stg</sub>	Storage Temperature	-55 to 150	°C
T <sub>j</sub>	Operating Junction Temperature		

(■) Pulse width limited by safe operating area

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case Max	2.5	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient Max	100	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>CASE</sub> = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>BR(CES)</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 250 µA, V <sub>GE</sub> = 0	600			V
I <sub>CES</sub>	Collector cut-off (V <sub>GE</sub> = 0)	V <sub>CE</sub> = Max Rating, T <sub>C</sub> = 25 °C V <sub>CE</sub> = Max Rating, T <sub>C</sub> = 125 °C			50 100	µA µA
I <sub>GES</sub>	Gate-Emitter Leakage Current (V <sub>CE</sub> = 0)	V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GE(th)</sub>	Gate Threshold Voltage	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 250 µA	5		7	V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	V <sub>GE</sub> = 15V, I <sub>C</sub> = 3 A V <sub>GE</sub> = 15V, I <sub>C</sub> = 3 A, T <sub>j</sub> = 125°C		2.4 1.9	2.8	V V

(#) Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

**ELECTRICAL CHARACTERISTICS (CONTINUED)**  
**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}$	Forward Transconductance	$V_{CE} = 25\text{ V}$ , $I_C = 3\text{ A}$		2.4		S
$C_{ies}$ $C_{oes}$ $C_{res}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{CE} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GE} = 0$		220 50 5.6		pF pF pF
$Q_g$ $Q_{ge}$ $Q_{gc}$	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 480\text{ V}$ , $I_C = 3\text{ A}$ , $V_{GE} = 15\text{ V}$		14 3.3 8	19	nC nC nC
$t_{scw}$	Short Circuit Withstand Time	$V_{ce} = 0.5\text{ BV}_{ces}$ , $V_{GE} = 15\text{ V}$ , $T_j = 125^\circ\text{C}$ , $R_G = 10\ \Omega$	10			$\mu\text{s}$

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{CC} = 480\text{ V}$ , $I_C = 3\text{ A}$ $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$		13.5 4.5		ns ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{CC} = 480\text{ V}$ , $I_C = 7\text{ A}$ , $R_G = 10\ \Omega$ $V_{GE} = 15\text{ V}$ , $T_j = 125^\circ\text{C}$		500		A/ $\mu\text{s}$
$E_{on}$	Turn-on Switching Losses			30		$\mu\text{J}$

**SWITCHING OFF**

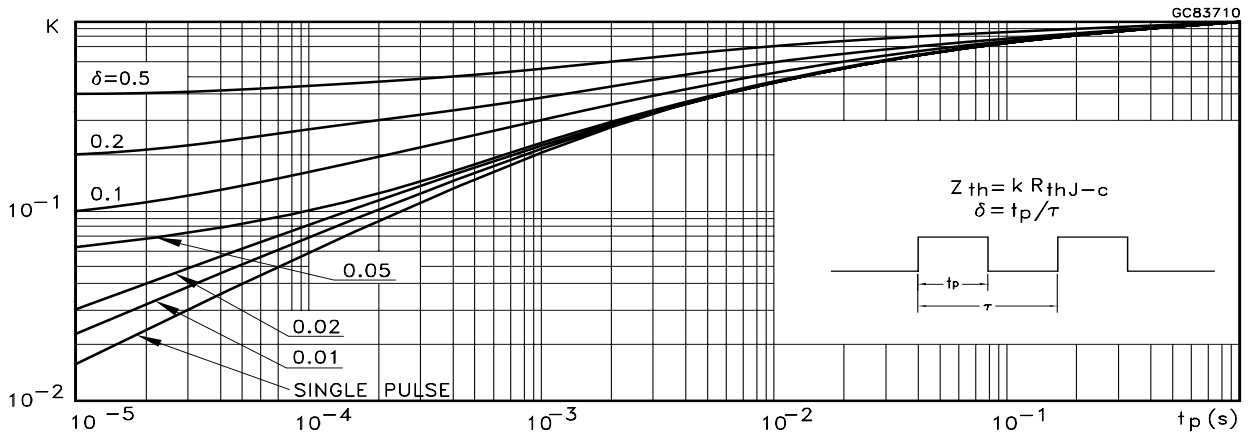
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_c$ $t_r(V_{off})$ $t_{d(off)}$ $t_f$ $E_{off(**)}$ $E_{ts}$	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 480\text{ V}$ , $I_C = 3\text{ A}$ , $R_{GE} = 10\ \Omega$ , $V_{GE} = 15\text{ V}$		86 20 32 85 50 78		ns ns ns ns $\mu\text{J}$ $\mu\text{J}$
$t_c$ $t_r(V_{off})$ $t_{d(off)}$ $t_f$ $E_{off(**)}$ $E_{ts}$	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 480\text{ V}$ , $I_C = 3\text{ A}$ , $R_{GE} = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ $T_j = 125^\circ\text{C}$		190 55 90 130 110 140		ns ns ns ns $\mu\text{J}$ $\mu\text{J}$

Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by max. junction temperature.  
(\*\*) Losses include Also the Tail (Jedec Standardization)

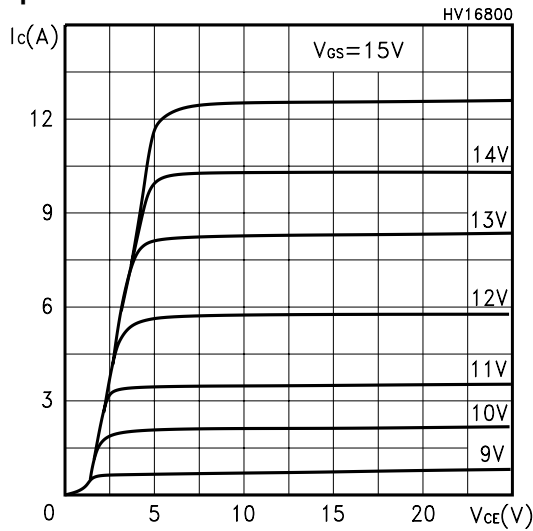
**COLLECTOR-EMITTER DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_f$ $I_{fm}$	Forward Current Forward Current pulsed				1.5 12	A A
$V_f$	Forward On-Voltage	$I_f = 1.5\text{ A}$ $I_f = 1.5\text{ A}$ , $T_j = 125^\circ\text{C}$		1.6 1.3	2.1	V V
$t_{rr}$ $Q_{rr}$ $I_{rrm}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 1.5\text{ A}$ , $V_R = 35\text{ V}$ , $T_j = 125^\circ\text{C}$ , $di/dt = 100\text{ A}/\mu\text{s}$		95 110 2.7		ns nC A

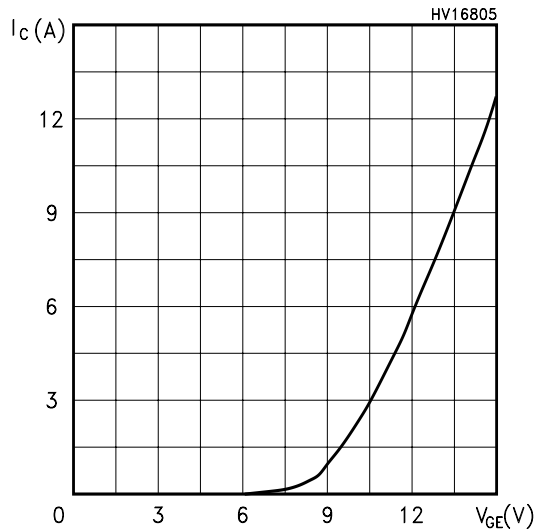
Thermal Impedance



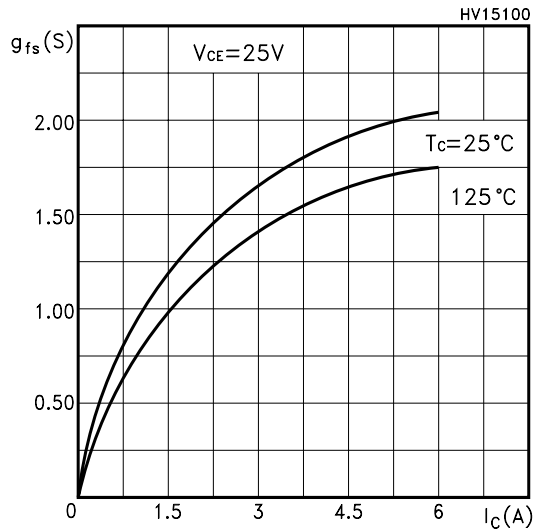
Output Characteristics



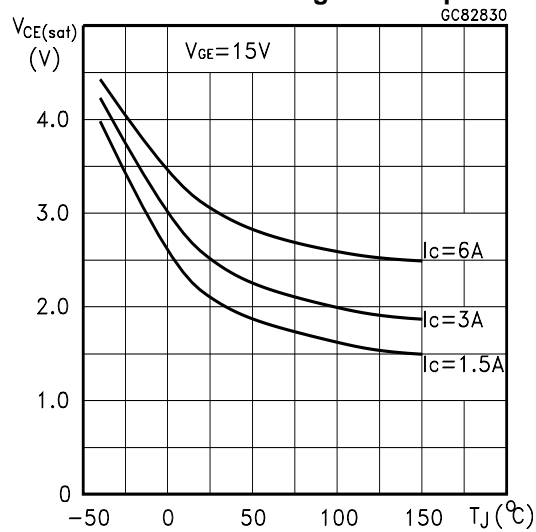
Transfer Characteristics



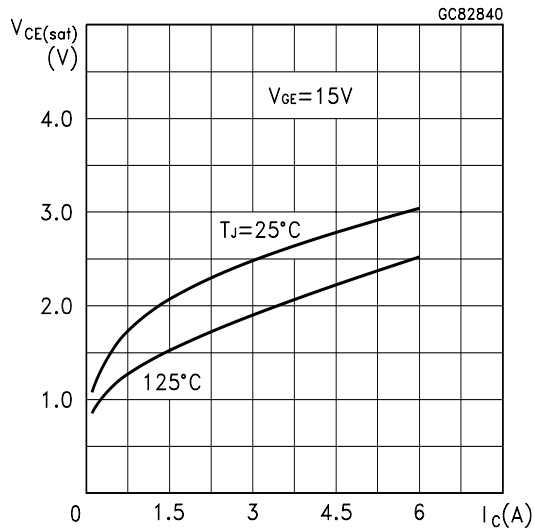
Transconductance



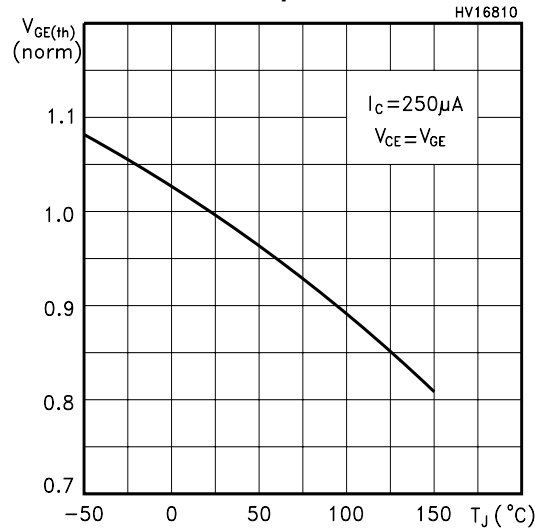
Collector-Emitter On Voltage vs Temperature



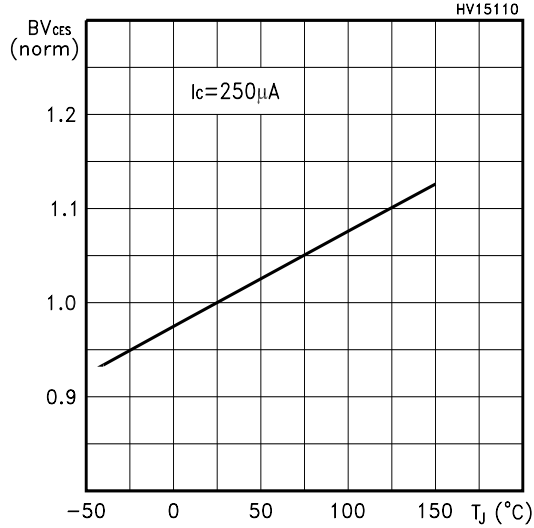
Collector-Emitter On Voltage vs Collector Current



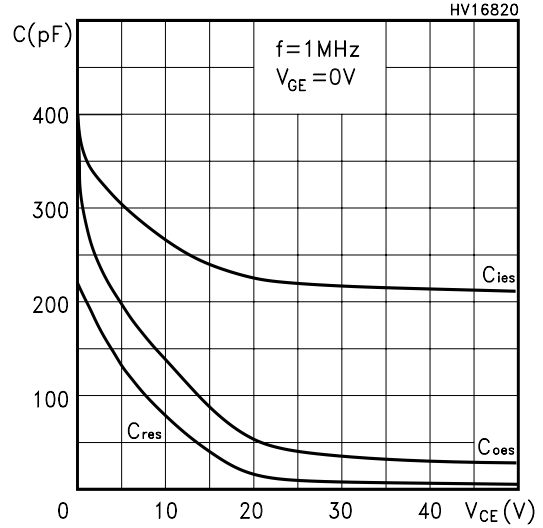
Gate Threshold vs Temperature



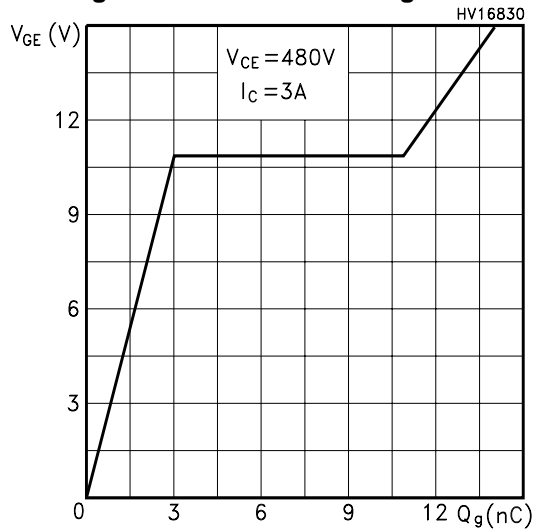
Normalized Breakdown Voltage vs Temperature



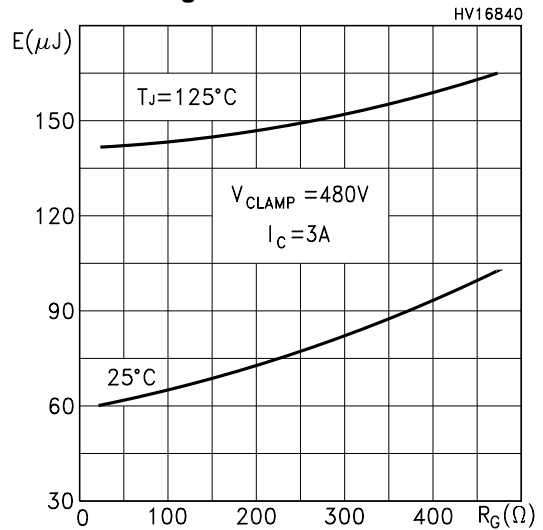
Capacitance Variations



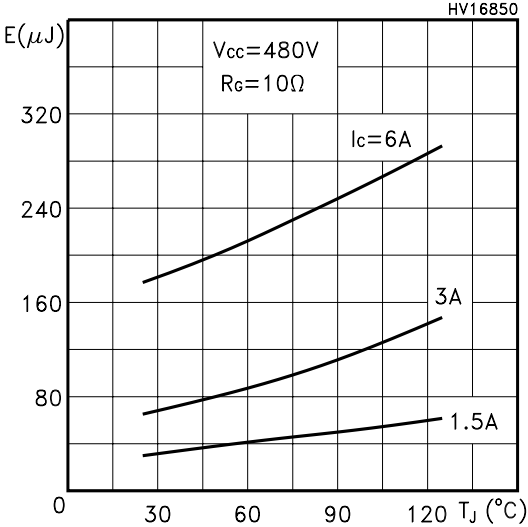
Gate Charge vs Gate-Emitter Voltage



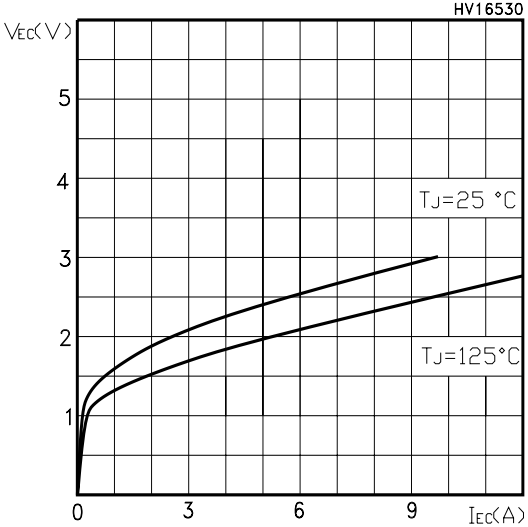
Total Switching Losses vs Gate Resistance



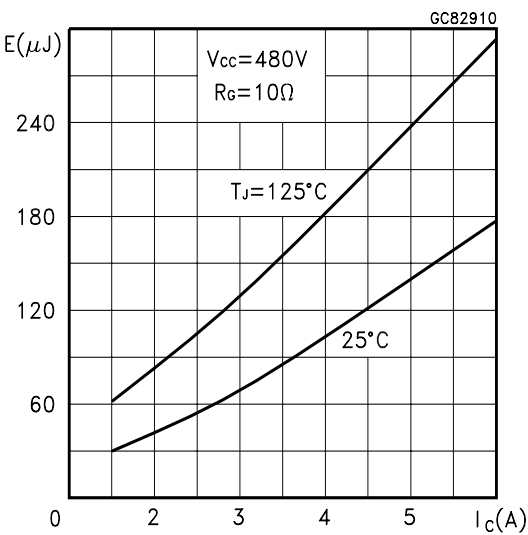
Total Switching Losses vs Temperature



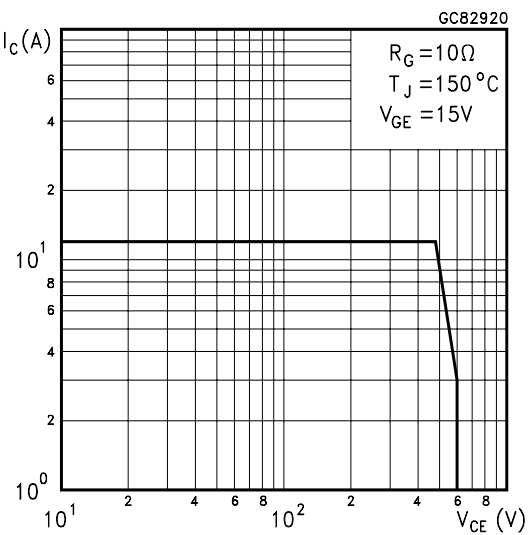
Emitter-collector Diode Characteristics



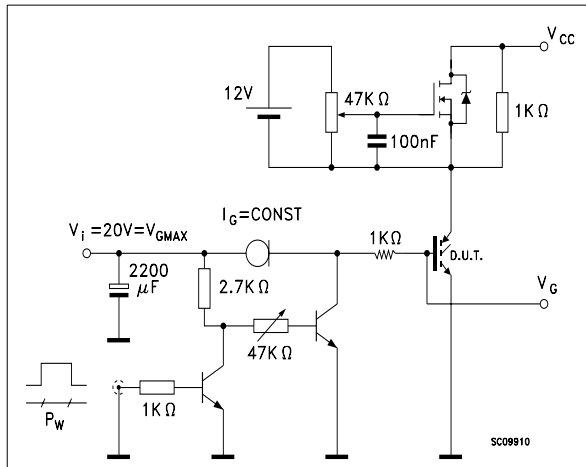
Total Switching Losses vs Collector Current



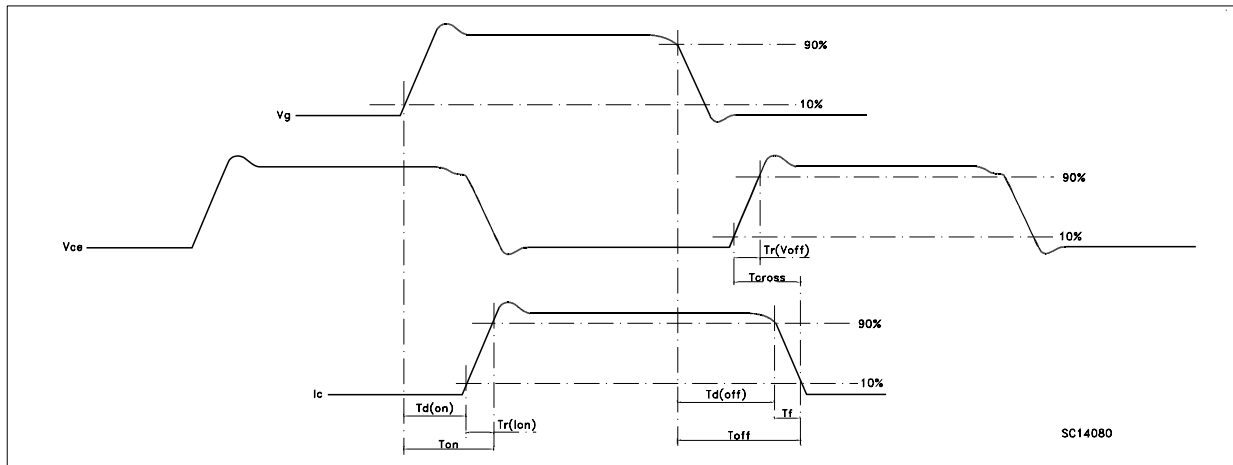
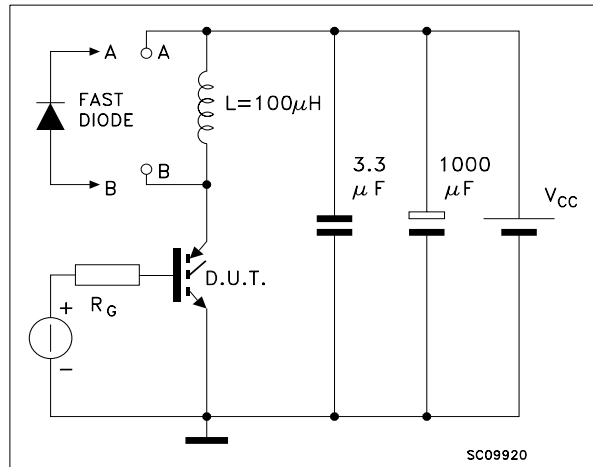
Switching Off Safe Operating Area



**Fig. 1: Gate Charge test Circuit**

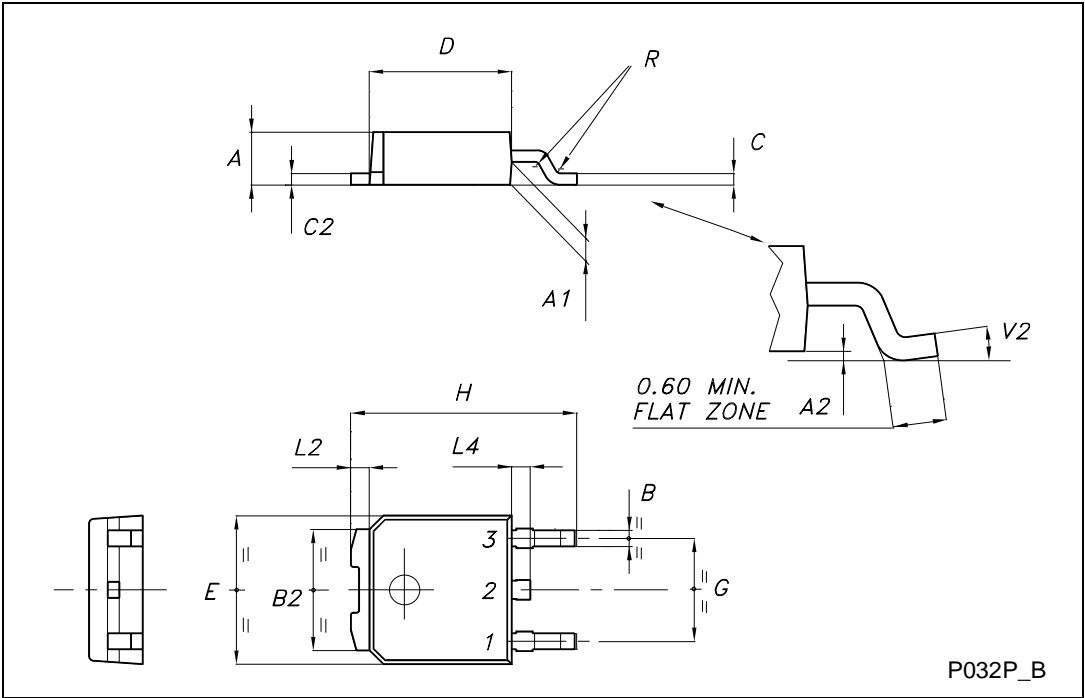


**Fig. 2: Test Circuit For Inductive Load Switching**



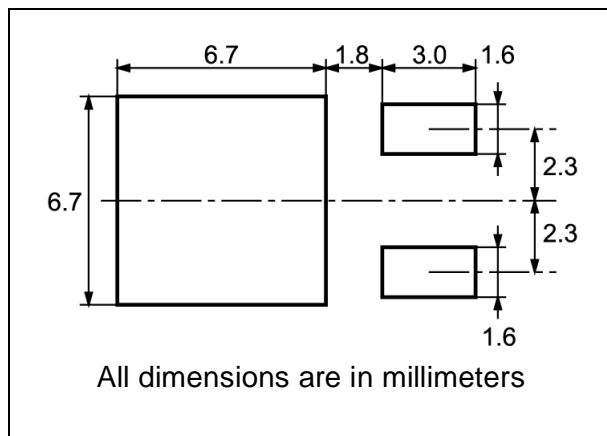
TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°

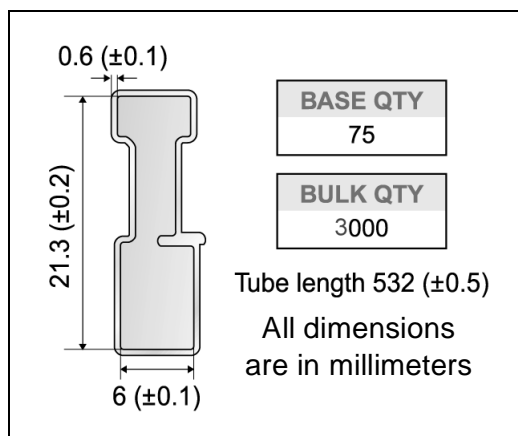




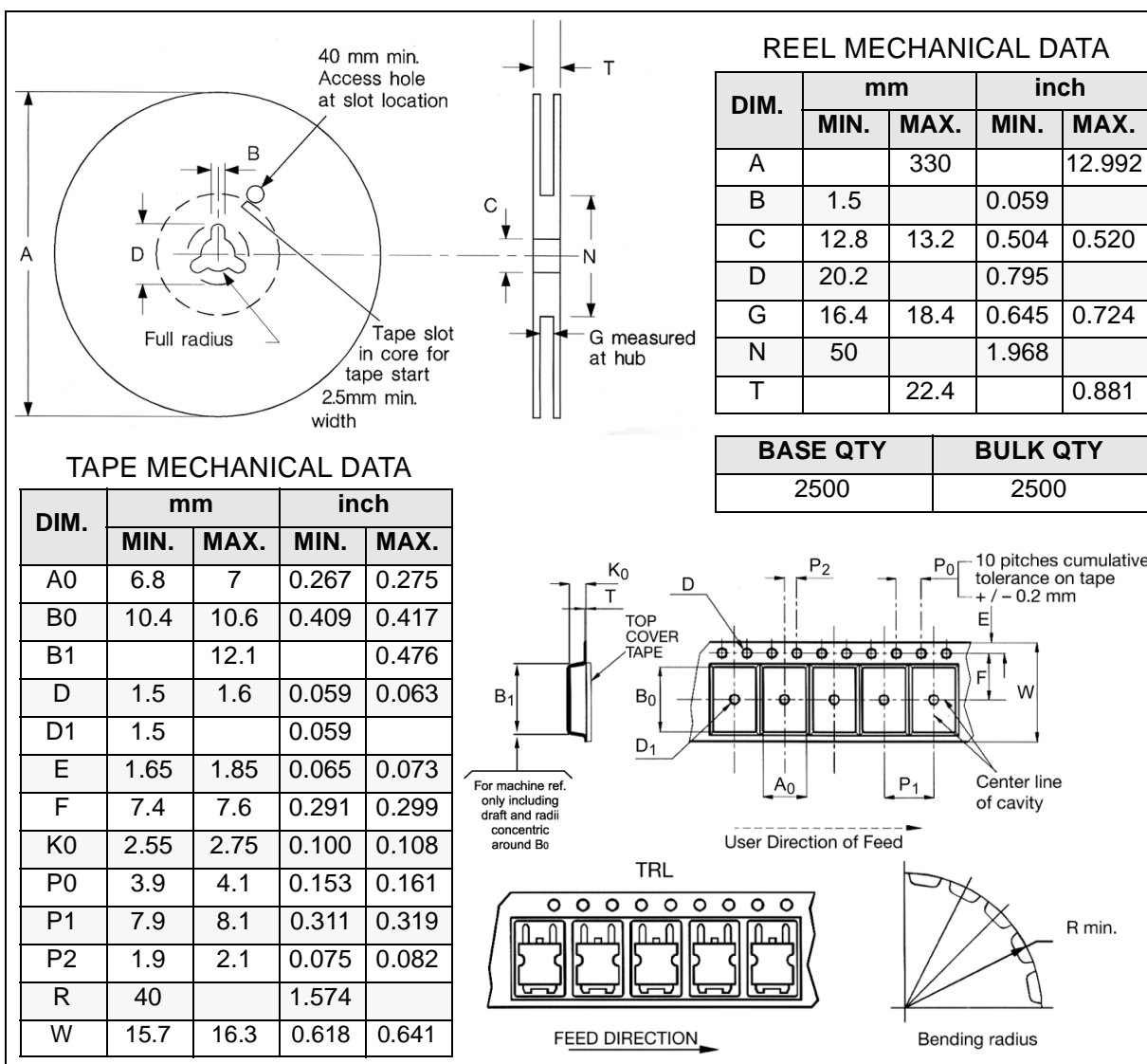
## DPAK FOOTPRINT



## TUBE SHIPMENT (no suffix)\*



## TAPE AND REEL SHIPMENT (suffix "T4")\*



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